

In the Specification

The paragraph beginning at line 20 on page 12 has been amended as follows:

An insulating layer 128, for example borophosphosilicate glass (BPSG), is formed over the word lines and is planarized as shown. An antireflective coating layer or layers (not shown) might preferably comprise an outermost portion of layer 128, and comprise silicon oxynitride which can also function as a diffusion barrier to hydrogen and other gases. Capacitor container openings 130 and 131 are formed within insulative layer 128 over source/drain diffusion regions 120 and 124, respectively, and the associated conductive covering regions 134. Exemplary openings 130 and 131 comprise trenches. A capacitor storage node layer 136 is formed within container openings 130 and 131 in electrical connection with source/drain diffusion regions 120 and 124 through conductive covering/plugging material 134. Such can be planarized back to be isolated within the container openings as shown. Example materials include conductively doped polysilicon, metal and metal compounds, with conductive metal oxides being preferred materials. Example conductive metal oxides include ruthenium oxide, iridium oxide, and rhodium oxide.